

Notice of References Cited	Application/Control No.	Applicant(s)/Patent Under Reexamination	
	10/611,992	RYOU, JAE-HYUN	
	Examiner	Art Unit	Page 1 of 1
ARMANDO RODRIGUEZ	2828		

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,765,238 b2	07-2004	Chang et al.	257/104
*	B	US-2004/0161013 a1	08-2004	Bour et al.	372/096
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	sEKIGUCHI ET AL, LONG WAVELENGTH GaInAsP/InP laser with n-n contacts using AlAs/InP hole injecting tunnel junction, Jpn. J. Appl. Phys., April 15, 199, Volume 38, pp. L443-L445.
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.